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# P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
- 60	0.107 at V <sub>GS</sub> = - 10 V	- 30 <sup>d</sup>			
	0.130 at V <sub>GS</sub> = - 4.5 V	- 20 <sup>d</sup>			

## **FEATURES**

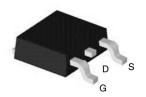
- DT-Trench Power MOSFET
- 100 % RgandUIS Tested
- AEC-Q101 Qualified for Automotive Applications



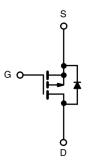
## **APPLICATIONS**

Load Switch





Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V <sub>DS</sub>	- 60	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	V			
Continuous Drain Current (T <sub>.1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	l <sub>D</sub>	- 30 <sup>d</sup>	A		
Continuous Drain Current (1) = 175 C)	T <sub>C</sub> = 125 °C	ט'	- 18			
Pulsed Drain Current	I <sub>DM</sub>	- 90				
Avalanche Current	I <sub>AS</sub>	- 25				
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	106	mJ		
Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	121 <sup>c</sup>	W		
rower Dissipation	T <sub>A</sub> = 25 °C	' D	2.7 <sup>b, c</sup>			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>b</sup>	t ≤ 10 s	- R <sub>thJA</sub>	12	15	°C/W	
Junction-to-Ambient	Steady State		35	45		
Junction-to-Case		R <sub>thJC</sub>	0.8	1.1		

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



Parameter Sy		Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage V <sub>DS</sub>		V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 60			v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1	- 1 - 3			
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V			- 1	μА	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50		
		V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 100	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -10 V	- 50			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A		0.107	0.119	131 155	
	P	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 125 °C			0.131		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 150 °C			0.155		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.130	0.145		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 10A		11		S	
Dynamic <sup>b</sup>	•						
Input Capacitance	C <sub>iss</sub>			1563			
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 25 V, f = 1 MHz		210		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			75			
Total Gate Charge <sup>c</sup>	Qg			20	28		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -40 \text{ A}$		11		nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			13			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -30 \text{ V}, R_{L} = 0.6 \Omega$		13		ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 40 A, $V_{GEN}$ = - 10 V, $R_G$ = 6 $\Omega$		35		115	
Fall Time <sup>c</sup>	t <sub>f</sub>			15			
Source-Drain Diode Ratings and Cha	aracteristics <sup>-</sup>	Γ <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>				- 30	А	
Pulsed Current	I <sub>SM</sub>				- 60	^	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = -30 A, V <sub>GS</sub> = 0 V		- 1	- 1.6	V	
		I <sub>F</sub> = - 30 A, dI/dt = 100 A/μs		25	33	ns	

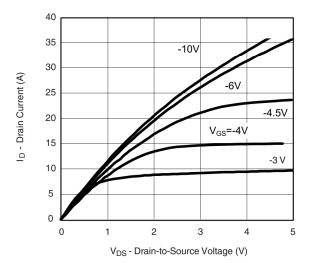
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.

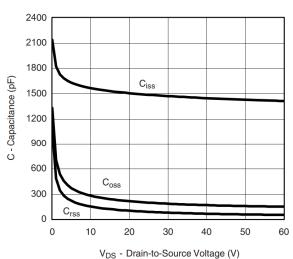
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



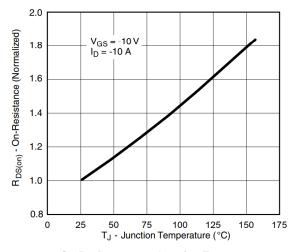
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



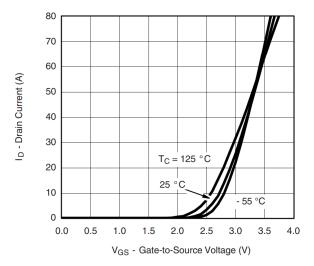
#### **Output Characteristics**



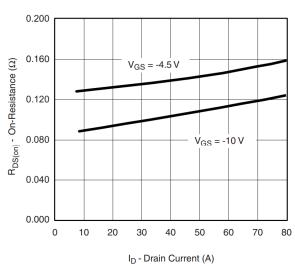
Capacitance



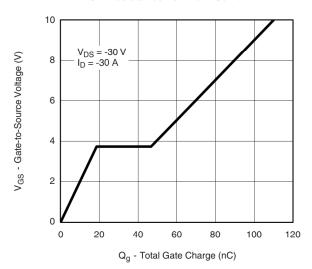
On-Resistance vs. Junction Temperature



#### **Transfer Characteristics**



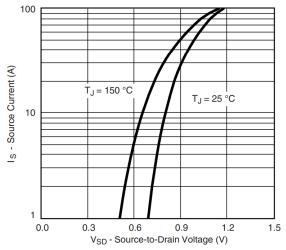
On-Resistance vs. Drain Current



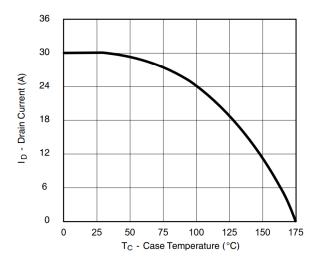
Gate Charge



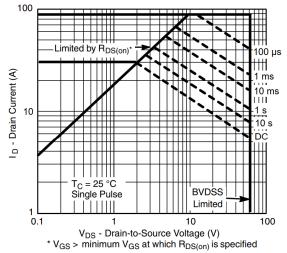
# **TYPICAL CHARACTERISTICS**



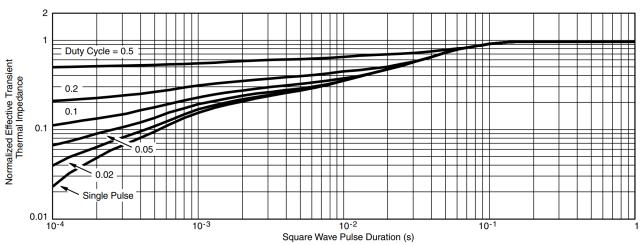
Source-Drain Diode Forward Voltage



**Drain Current vs. Case Temperature** 



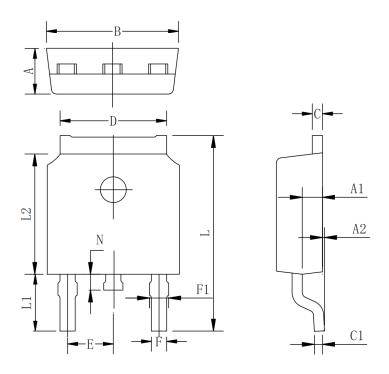
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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# **TO-252-2L PACKAGE OUTLINE**



# COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
C	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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